



A.P. 12822

Attorney Docket No. SEL 126

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

(AF) #15/B
T. BELL
10-17-01

In Re Application of:

Takeshi FUKUNAGA

Serial No.: 09/262,657 ✓

Filed: March 4, 1999

Examiner: Mark Prenty

Art Unit: 2822

For: SEMICONDUCTOR DEVICE AND
METHOD FOR MANUFACTURING
SAME

I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, Washington, D.C. 20231 on October 4, 2001

Name: Bobbi Wilson

Signature: [Signature]

[Signature]
1-23-02

Commissioner for Patents
Washington, D.C. 20231

AMENDMENT AFTER FINAL

Dear Sir:

Please amend the above-identified application as follows:

In the Claims:

Please amend Claims 1, 30, 31, 33, 34, 36, and 37 as follows:

1. (Twice Amended) A semiconductor device comprising:

a substrate;

a first thin film transistor having a first active layer comprising $\text{Si}_{1-x}\text{Ge}_x$ where $0 < x < 1$

formed over said substrate; and

a second thin film transistor having a second active layer comprising silicon formed over said substrate wherein said second active layer is not intentionally added with germanium.

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